IN THE CLAIMS:

Please amend the claims as follows:

1) (Currently Amended) A micromechanical device that is capable of movement due to a flexible portion and comprises [having at least a portion comprising] a nitride compound and a late transition metal, wherein the nitride compound and late transition metal are in the same film or layer and wherein the film or layer is a ternary or higher system deposited by chemical or physical vapor deposition.

2) (Original) The micromechanical device of claim 1, wherein the nitride compound is a nitride of silicon, boron or aluminum.

3) (Original) The micromechanical device of claim 2, wherein the nitride compound is a silicon nitride or boron nitride.

4) (Original) The micromechanical device of claim 1, wherein the late transition metal is selected from the groups 8B or 1B of the periodic table.

5) (Original) The micromechanical device of claim 1, wherein the late transition metal is a ferromagnetic metal.

6) (Original) The micromechanical device of claim 1, which is a MEMS sensor or actuator.

7) (Original) The micromechanical device of claim 1, wherein the late transition metal is a noble metal.

8) (Original) The micromechanical device of claim 1, wherein the late transition metal is Co, Ni, Pd, Pt, Ag or Au.

9) (previously presented) The micromechanical device of claim 1, wherein the nitride comprises less than 0.1% oxygen.

10) (previously presented) The micromechanical device of claim 1, wherein the nitride is an oxynitride that comprises up to 10% oxygen.

11) (Original) The micromechanical device of claim 1, wherein at least a flexible portion comprises the nitride compound and the late transition metal.

12) (Original) The micromechanical device of claim 1, comprising a substrate, a movable element formed in or on the substrate and a hinge for allowing movement of the

movable element relative to the substrate.

13) (Original) The micromechanical device of claim 12, wherein the substrate is a semiconductor or light transmissive substrate.

14) (Original) The micromechanical device of claim 12, wherein the movable element and/or the hinge are formed of the nitride compound and the late transition metal.

15) (Original) The micromechanical device of claim 14, further comprising posts or walls for connecting the movable element to the substrate via the hinge.

16) (Original) The micromechanical device of claim 12, wherein the hinge is a sputtered hinge.

17) (Original) The micromechanical device of claim 12, wherein the device is a micromirror device with said movable element having a reflective layer thereon or therein.

18) (Original) The micromechanical device of claim 12, which is a sensor.

19) (Original) The micromechanical device of claim 17, wherein the reflective layer comprises Al, Ti or Au.

20) (Original) The micromechanical device of claim 17, wherein the micromirror device is a light beam steering device.

21) (previously presented) The micromechanical device of claim 20, wherein the light beam steering device is within an optical switch.

22) (Original) The micromechanical device of claim 17, wherein the micromirror device is part of a micromirror array in a display.

23) (Original) The micromechanical device of claim 22, wherein the display is a direct view or projection display.

24) (previously presented) A micromechanical device selected from a micromirror, a MEMS switch and a MEMS sensor, having a movable portion and a flexible portion, wherein at least one of the movable portion and flexible portion comprise a ceramic compound and a late transition metal, wherein the ceramic compound and late transition metal are in the same film or layer and wherein the film or layer is a ternary or higher system deposited by chemical or physical vapor deposition.

55) (Currently Amended) A micromechanical device that is capable of movement due to a flexible portion comprising a late transition metal and an element from groups 3A to 6A of the periodic table and with the flexible portion being formed by chemical or physical vapor deposition, wherein the late transition metal and the element from groups 3A to 6A of the periodic table are in the same film or layer and wherein the film or layer is a ternary or higher system deposited by chemical or physical vapor deposition.

56) (Original) The micromechanical device of claim 55, wherein the late transition metal is selected from groups 8B or 1B of the periodic table.

57) (Original) The micromechanical device of claim 55, further comprising an element from groups 3A to 6A of the periodic table.

58) (Original) The micromechanical device of claim 57, comprising more than one element from groups 3A to 6A.

59) (Original) The micromechanical device of claim 58, comprising two or more elements from the first two rows of groups 3A to 6A.

60) (Original) The micromechanical device of claim 59, wherein one of the two or more elements is nitrogen.

61) (Original) The micromechanical device of claim 60, wherein another of the two or

more elements is aluminum, boron, silicon carbon or oxygen.

62) (Original) The micromechanical device of claim 61, wherein the late transition metal is a ferromagnetic metal.

63) (previously presented) The micromechanical device of claim 55, wherein the late transition metal is a noble metal.

64) (Currently Amended) A micromechanical device that is capable of movement due to a flexible portion and comprises [comprising] a ceramic compound and a late transition metal, wherein the ceramic compound and late transition metal are a ternary or higher system within a common layer.

65) (Original) The micromechanical device of claim 64, wherein the ceramic compound is a nitride and/or oxide compound, and the late transition metal is selected from either of groups 8B or 1B in the periodic table.

66) (Original) The micromechanical device of claim 65, wherein the device comprises in at least one element from groups 8B or 1B and two or more elements from the first two rows of groups 3A to 6A of the periodic table.